









# **B1D04065KF**

#### 650V ▲ 4A ▲ SIC SCHOTTKY DIODE

SILICON CARBIDE SIC SCHOTTKY DIODE ▲ THT type

Excellent surge capability
Easy paralleling due to positive V<sub>F</sub> temperature coefficient

Temperature independent switching

Low forward voltage

TO-220F-2L package ▲ Electrical insulated mounting tab

Item (T <sub>c</sub> = 25°C, unless otherwise noted)		Characteristics
Operating Temperature Range	Tı	-55°C to +175°C
Storage Temperature Range	Ts	-55°C to +175°C
Repetitive Peak Reverse Voltage	$V_{RRM}$	650V
Continuous Forward Current at T <sub>C</sub> = 140°C	I <sub>F</sub>	4A
Total Capacitive Charge (T <sub>J</sub> = 25°C)	$\mathbf{Q}_{C}$	12nC
Capacitance Stored Energy (V <sub>R</sub> = 400V)	Ec	3µЈ
Diode Forward Voltage (T <sub>J</sub> = 175°C, I <sub>F</sub> = 4A)	$V_{F}$	1.7V
Power Dissipation	P <sub>TOT</sub>	30W

#### **APPLICATIONS**

EV Charging	Industrial Inverters	Motors & Drives	Power Factor Correction	Renewable Energy	SMPS	UPS
<b>₹</b> /•			PFC	*		

#### **PIN DESCRIPTION**

Circuit Diagram	Outline • Front View	Pin No.	Description
	1 2	1 2	Cathode Anode

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## ABSOLUT MAXIMUM RATINGS ▲ T<sub>C</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol		Unit
Repetitive Peak Reverse Voltage		$V_{RRM}$	650	V
Non-Repetitive Peak Reverse Voltage		$V_{RSM}$	650	V
Continuous Forward Current	T <sub>C</sub> = 25°C	I <sub>F</sub>	10	Α
Continuous Forward Current	$T_C = 140^{\circ}C$	I <sub>F</sub>	4	Α
Non-Repetitive Forward Surge Current	$T_C$ = 25°C, $t_p$ = 10ms, Half Sine Wave	I <sub>FSM</sub>	30	Α
I <sup>2</sup> t Value	$T_C = 25^{\circ}C$ , $t_p = 10$ ms	∫i²dt	4.5	$A^2s$
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>TOT</sub>	30	W
Power Dissipation	$T_C = 110^{\circ}C$	$P_{TOT}$	13	W
Operating Junction Temperature		T <sub>J</sub>	-55 to +175	°C
Storage Temperature Range		$T_{STG}$	-55 to +175	°C
TO-220 Mounting Torque	M3 Screw		0.7	Nm

#### **ELECTRICAL CHARACTERISTICS**

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Static Characteristics						
DC Blocking Voltage	T <sub>J</sub> = 25°C	$V_{DC}$	650			V
Diode Forward Voltage	$I_F = 4A, T_J = 25^{\circ}C$	$V_{F}$		1.40	1.60	V
Diode Forward Voltage	I <sub>F</sub> = 4A, T <sub>J</sub> = 175°C	$V_{F}$		1.70	2.80	V
Reverse Current	$V_R = 650V, T_J = 25^{\circ}C$	$I_R$		1	120	μΑ
Reverse Current	$V_R = 650V, T_J = 175^{\circ}C$	I <sub>R</sub>		10	200	μΑ
Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Dynamic Characteristics						
Dynamic Characteristics	V <sub>R</sub> = 400V, T <sub>J</sub> = 25°C					
Dynamic Characteristics  Total Capacitive Charge	$V_{R} = 400V, T_{J} = 25^{\circ}C$ $Q_{C} = \int_{0}^{V_{R}} C(V) dV$	Qc		12		nC
		Q <sub>c</sub>		12 181		nC pF
Total Capacitive Charge	$Q_C = \int_0^{V_R} C(V) dV$					
Total Capacitive Charge  Total Capacitance	$Q_C = \int_0^{V_R} C(V) dV$ $V_R = 1V, f = 1MHz, T_J = 25^{\circ}C$	С		181		pF

## THERMAL RESISTANCE PERFORMANCE

Item	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance, Junction to Case	$R_{\theta,JC}$		4.996		K/W



#### REFERENCE DATA A TYPICAL PERFORMANCE

Fig. 1 • Typical Forward Characteristics I<sub>F</sub> vs. V<sub>F</sub>

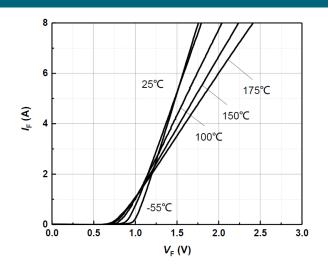


Fig. 2 • Typical Reverse Current I<sub>R</sub> as function of Reverse Voltage V<sub>R</sub>

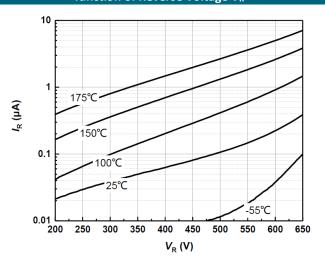


Fig. 3 • Diode Forward Current  $I_F$  as function of Case Temperature  $T_C$  (D = Duty Cycle)

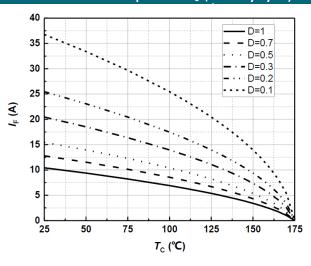


Fig. 4 • Typical Capacitance C as function of Reverse Voltage  $V_R$ ,  $C = f(V_R)$ ,  $T_J = 25^{\circ}C$ , f = 1MHz

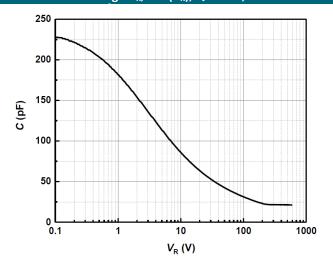


Fig. 5 • Typical Reverse Charge Q<sub>C</sub> as function of Reverse Voltage V<sub>R</sub>

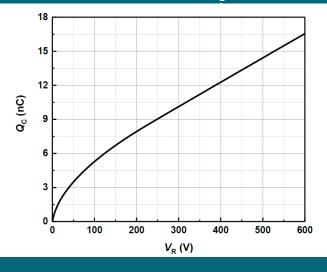
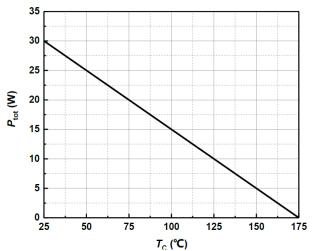


Fig. 6 • Power Dissipation P<sub>TOT</sub> as function of Case Temperature T<sub>C</sub>



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#### REFERENCE DATA A TYPICAL PERFORMANCE

Fig. 7 • Capacitance Stored Energy

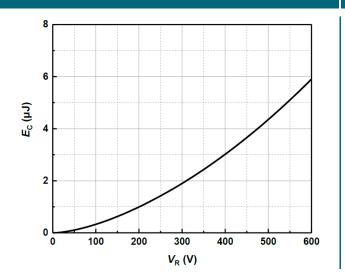
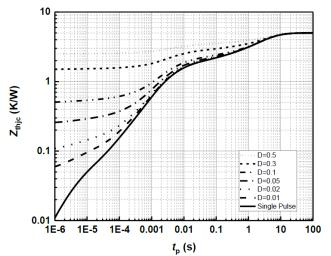
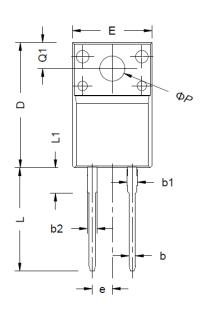


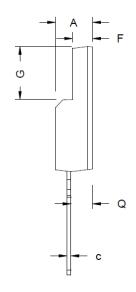
Fig. 8 • Maximum Transient Thermal Impedance, Z<sub>thjc</sub> = f(t), Parameter: D = t/T

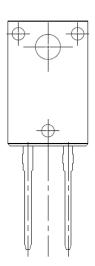




## **PACKAGE OUTLINE**









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	4.60	4.70	4.80
b	0.70	0.80	0.91
b1	1.20	1.30	1.47
b2	1.10	1.20	1.30
С	0.45	0.50	0.63
D	15.80	15.87	15.97
D	15.15	15.45	15.75
е		2.54 BSC	
E	10.00	10.10	10.30

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F	2.44	2.54	2.64
G	6.50	6.70	6.90
L	12.90	13.10	13.30
L	12.70	-	13.70
L1	3.13	3.23	3.33
Q	2.65	2.75	2.85
Q1	3.20	3.30	3.40
ØΡ	2.08	3.18	3.28

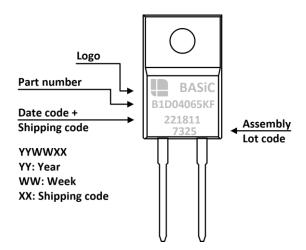
TO-220F-2L package ▲ Epoxy meets UL94-V0

## **ORDERING INFORMATION**

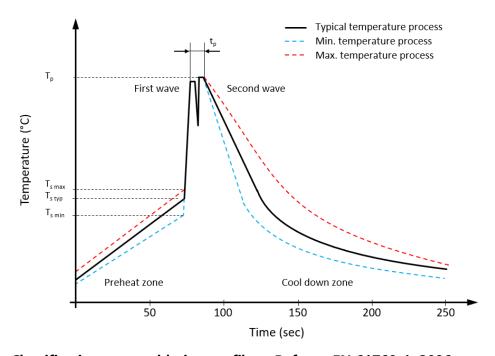
Part Number	Package	Packing	Tube Qty.	Inner Box Qty.	Outer Box Qty.
B1D04065KF	TO220F-2L	Tube	50pcs	500pcs	5,000pcs



#### **PART MARKING**



## RECOMMENDED WAVE SOLDERING PROFILE & THT PACKAGE



## Classification wave soldering profile ▲ Refer to EN 61760-1: 2006

Profile Features		Value ▲ Sn-Pb Assembly	Value ▲ Pb-free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	100 °C
Preheat temperature typical	T <sub>s typ</sub>	120 °C	120 °C
Preheat temperature max.	$T_{s  max}$	130 °C	130 °C
Preheat time $t_s$ from $T_{smin}$ to $T_{smax}$	ts	70 seconds	70 seconds
Peak temperature	Tp	235 °C to 260 °C	245 °C to 260 °C
Time of actual peak temperature	t <sub>p</sub>	Max. 10 seconds Max. 5 second each wave	Max. 10 seconds Max. 5 second each wave
Ramp-down date min.		~ 2 °C/second	~ 2 °C/second
Ramp-down rate typical		~ 3.5 °C/second	~ 3.5 °C/second
Ramp-down rate max.		~ 5 °C/second	~ 5 °C/second
Time 25°C to 25°C		4 minutes	4 minutes

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#### **EVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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